TECHNICAL DATA DATA SHEET 4202, REV. -

HERMETIC FAST RECOVERY RECTIFIER HIGH VOLTAGE

Features:

- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- Very High Surge Capacity
- Very suitable for medium frequency applications (upto 10 kHz)
- Soft Reverse Recovery at Low and High Temperature
- Trr guaranteed lower than 2.5 msec
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings:

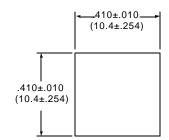
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	1100	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form, T _C = 65 °C	80	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 msec, sine pulse	720	А
Thermal Impedance	Z _{TH}	T _C = 25 °C	0.5	°C / W
Max. Junction Temperature	T _J	-	- 40 to + 165	°C
Max. Storage Temperature	T _{stg}	-	- 55 to + 175	°C

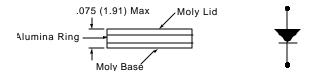
Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 80A, Pulse, T _J = 25 °C	1.25	1.4	V
	V_{F2}	@ 80A, Pulse, T _J = 125 °C	-	1.25	V
	I _{R1}	@V _R = 1000V, Pulse,	1.5	5.0	μΑ
		$T_J = 25 ^{\circ}C$			
Max. Reverse Current	I_{R2}	@V _R = 1000V, Pulse,	-	15	mA
		T _J = 125 °C			
Reverse Recovery Time	T_RR	$I_F = 40A$; di/dt = 25A / μ sec;	1.6	2.1	μsec
		V _R = 100V			
		$T_J = 25 ^{\circ}C$			
Reverse Recovery Current	I_{RM}	$I_F = 40A$; di/dt = 25A / μ sec;	27	40	Α
		V _R = 100V			
		T _J = 25 °C			
Max. Junction Capacitance	C _T	$@V_R = 0V, T_C = 25 ^{\circ}C$	650	-	pF
		$f_{SIG} = 1MHz,$			
		$I_{SIG} = 100 \text{mV (p-p)}$			

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MECHANICAL DIMENSIONS: In Inches / mm





SHD-3



TECHNICAL DATA

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